

a word line driver for coupling the activated write word line to a first voltage at its one end and setting the remaining write word lines to a second voltage in order to supply [a second] said first data write current [for generating said second data write magnetic field] in said data write operation;

coupling switches respectively coupled between each write word line and a plurality of write word lines of other memory cell rows, each of the coupling switches being turned ON when one of the two write word lines coupled thereto is activated; and

a data read circuit for supplying said data read current to one of said plurality of bit lines in said data read operation according to a column selection result, and conducting said data read operation based on a voltage change on said bit line corresponding to said column selection result, wherein

said word line driver sets each of said plurality of write word lines to a prescribed voltage in said data read operation.

REMARKS

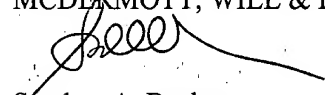
Claims 1-26 stand rejected under the judicially created doctrine of obviousness-type double patenting in view of U.S. Patent No. 6,349,054, claims 1-15. To expedite prosecution, submitted herewith is a Terminal Disclaimer to obviate this rejection.

Minor corrections are made to claims 12, 18 and 22 for improved clarity. These amendments do not limit claim scope for any reason related to patentability. Clean versions of the amended claims are appended hereto.

To the extent necessary, a petition for an extension of time under 37 C.F.R. 1.136 is hereby made. Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

Respectfully submitted,

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Clean Version of Amended Claims

12. The thin film magnetic memory device according to claim 10, wherein
said plurality of second data lines are provided respectively corresponding said
plurality of first data lines,
each of said dummy source lines respectively corresponding to said plurality of
second data lines is provided as a wiring common to a corresponding one of said plurality
of source lines, and
each of said dummy source line selection portions respectively corresponding to
said dummy source lines is common to a corresponding one of said source selection
portions.

18. A thin film magnetic memory device, comprising:
a plurality of memory cells arranged in a matrix, each of said plurality of memory
cells including a magnetic storage portion having its electric resistance value varying
according to a storage data level written by combination of first and second data write
magnetic fields;
a plurality of write word lines provided respectively corresponding to memory
cell rows, and selectively activated in data write operation to pass therethrough a first
data write current for generating said first data write magnetic field;
a plurality of source lines provided respectively corresponding to said memory
cell rows, and coupled to a first voltage at their respective one ends;

a plurality of bit lines provided respectively corresponding to memory cell columns, and selectively receiving a second data write current for generating said second data write magnetic field in said data write operation according to a column selection result; and

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a word line driver for coupling the activated write word line to a second voltage at its one end in said data write operation, wherein

said first data write current flows through a current path formed from said activated write word line and at least one of said plurality of source lines which is electrically coupled to said activated write word line at the other ends.

22. A thin film magnetic memory device, comprising:

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a plurality of memory cells arranged in a matrix, each of said plurality of memory cells including

a magnetic storage portion having its electric resistance value varying according to a storage data level written therein by combination of first and second data write magnetic fields, and

an access portion coupled in series with said magnetic storage portion, and selectively turned ON in data read operation to pass a data read current therethrough and turned OFF in data write operation, said thin film magnetic memory device further comprising:

a plurality of read word lines provided respectively corresponding to memory cell rows, for turning ON said access portion in said data read operation according to a row selection result;

a plurality of write word lines provided respectively corresponding to said memory cell rows, and selectively activated to pass therethrough a first data write current generating said first data write magnetic field in said data write operation;

a plurality of bit lines provided respectively corresponding to memory cell columns, each of said plurality of bit lines being electrically coupled to said plurality of write word lines through said memory cells;

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a word line driver for coupling the activated write word line to a first voltage at its one end and setting the remaining write word lines to a second voltage in order to supply said first data write current in said data write operation;

coupling switches respectively coupled between each write word line and a plurality of write word lines of other memory cell rows, each of the coupling switches being turned ON when one of the two write word lines coupled thereto is activated; and

a data read circuit for supplying said data read current to one of said plurality of bit lines in said data read operation according to a column selection result, and conducting said data read operation based on a voltage change on said bit line corresponding to said column selection result, wherein

said word line driver sets each of said plurality of write word lines to a prescribed voltage in said data read operation.
